

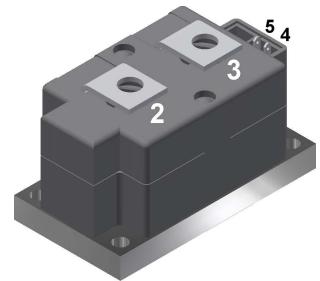
Thyristor Module

V_{RRM} = 1200 V
 I_{TAV} = 560 A
 V_T = 1.01 V

Single Thyristor

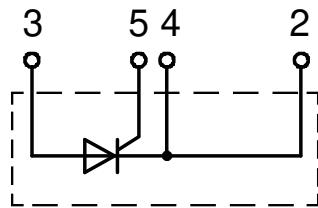
Part number

MCO500-12io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

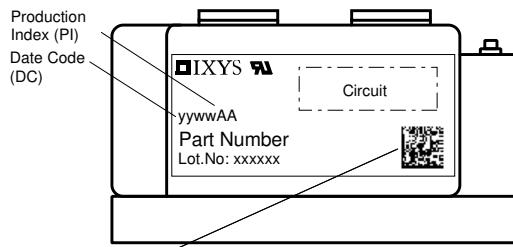
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Thyristor

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200 V$ $V_{R/D} = 1200 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		2 40	mA
V_T	forward voltage drop	$I_T = 500 A$	$T_{VJ} = 25^\circ C$		1.08	V
		$I_T = 1000 A$			1.27	V
		$I_T = 500 A$ $I_T = 1000 A$	$T_{VJ} = 125^\circ C$		1.01 1.24	V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 140^\circ C$		560	A
$I_{T(RMS)}$	RMS forward current	180° sine			880	A
V_{T0}	threshold voltage	$\left. \begin{array}{l} \text{slope resistance} \\ \end{array} \right\} \text{for power loss calculation only}$	$T_{VJ} = 140^\circ C$		0.80	V
r_T	slope resistance				0.38	mΩ
R_{thJC}	thermal resistance junction to case				0.072	K/W
R_{thCH}	thermal resistance case to heatsink			0.024		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		1600	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		17.0	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		18.4	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 140^\circ C$		14.5	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		15.6	kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		1.45	MA²s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		1.40	MA²s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 140^\circ C$		1.04	MA²s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		1.01	MA²s
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	876		pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^\circ C$		120	W
		$t_p = 300 \mu s$			60	W
					20	W
P_{GAV}	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^\circ C; f = 50 \text{ Hz}$	repetitive, $I_T = 1500 A$		100	A/μs
		$t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$				
		$I_G = 1 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 500 A$		500	A/μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ C$		1000	V/μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		2	V
			$T_{VJ} = -40^\circ C$		3	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		300	mA
			$T_{VJ} = -40^\circ C$		400	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ C$		0.25	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^\circ C$		400	mA
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		300	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ C$		2	μs
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 500 A; V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$	350		μs
		$di/dt = 10 A/\mu s$ $dv/dt = 50 V/\mu s$ $t_p = 200 \mu s$				

Package Y1

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			600	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				650		g
M_D	mounting torque		4.5		7	Nm
M_T	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air		terminal to terminal	16.0		mm
$d_{Spb/Apb}$			terminal to backside	25.0		mm
V_{ISOL}	isolation voltage	$t = 1$ second $t = 1$ minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600		V
				3000		V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

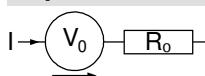
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCO500-12io1	MCO500-12io1	Box	2	463728

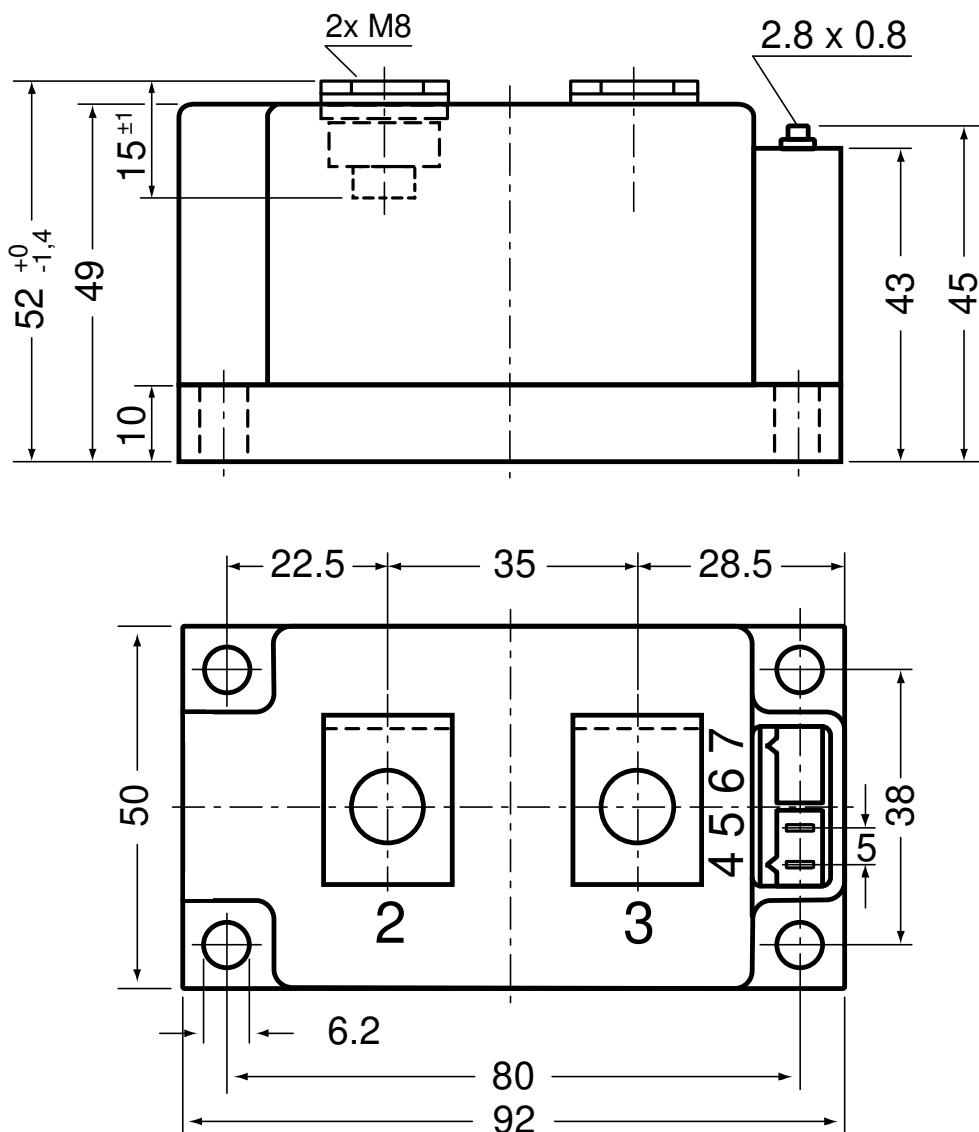
Similar Part	Package	Voltage class
MCO500-14io1	Y1-2-CU	1400
MCO500-16io1	Y1-2-CU	1600
MCO500-18io1	Y1-2-CU	1800
MCO600-20io1	Y1-2-CU	2000

MCO600-22io1	Y1-2-CU	2200
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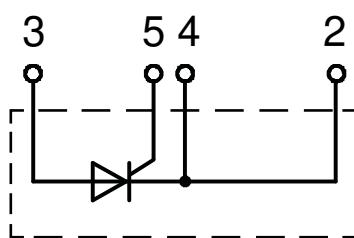
Equivalent Circuits for Simulation
^{*}on die level

 $T_{VJ} = 140^\circ\text{C}$

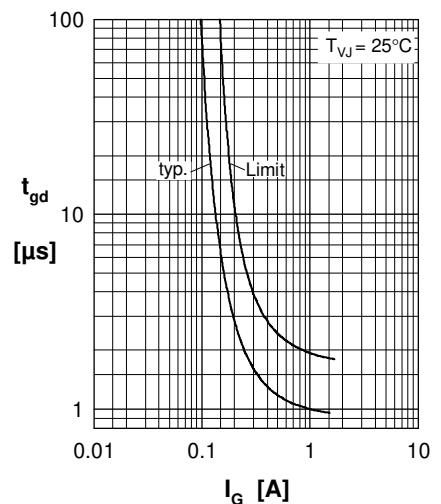
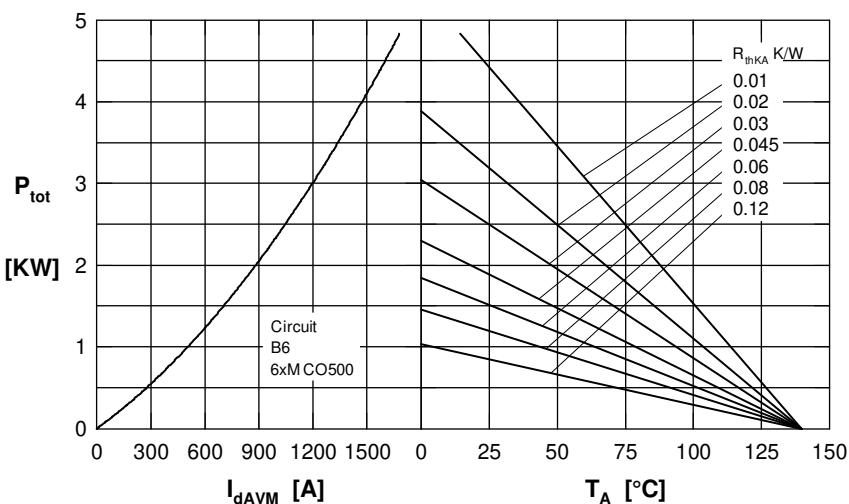
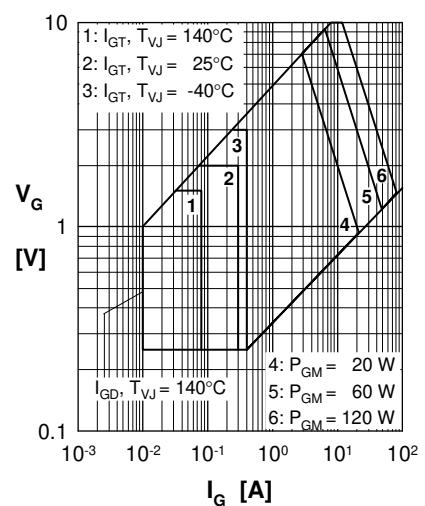
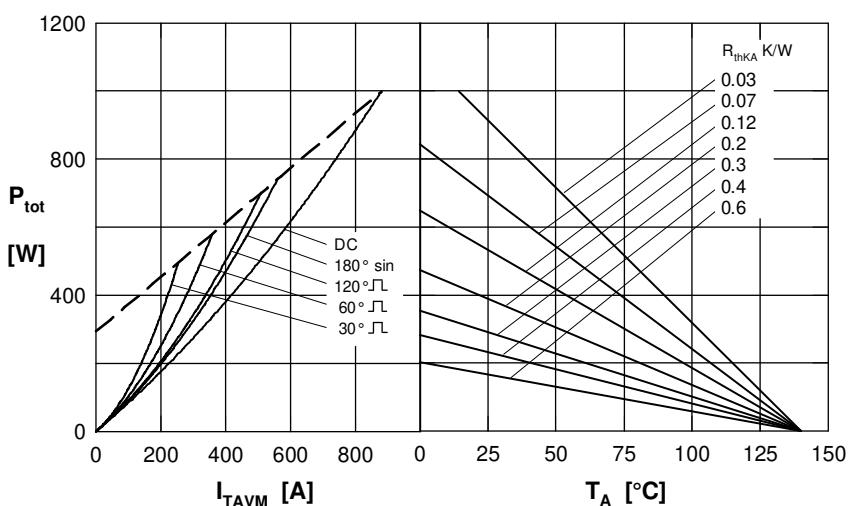
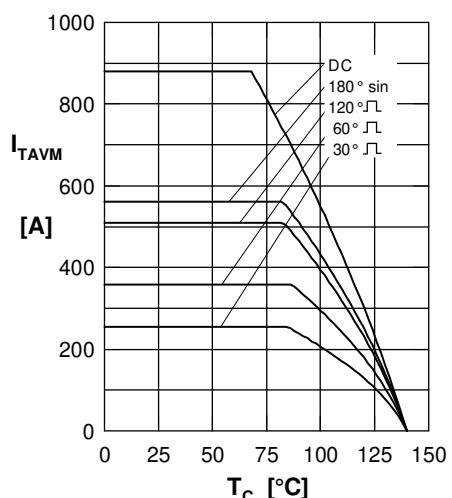
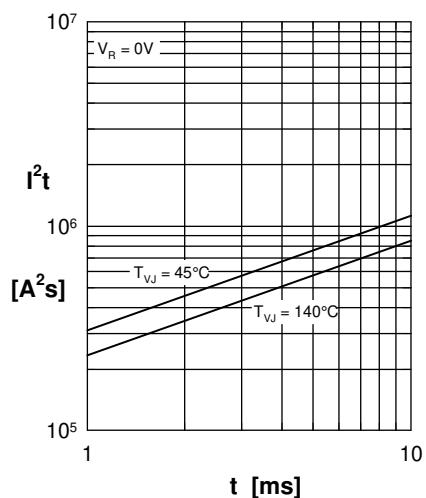
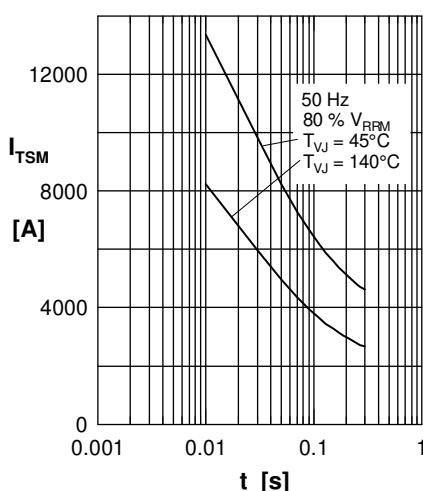
	Thyristor
$V_{0\ max}$	threshold voltage
$R_{0\ max}$	slope resistance * 0.22

Outlines Y1

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor



Thyristor

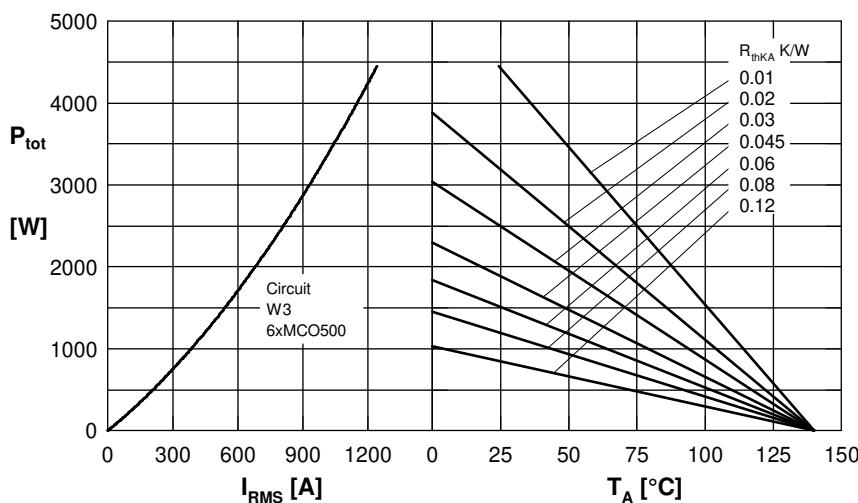


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

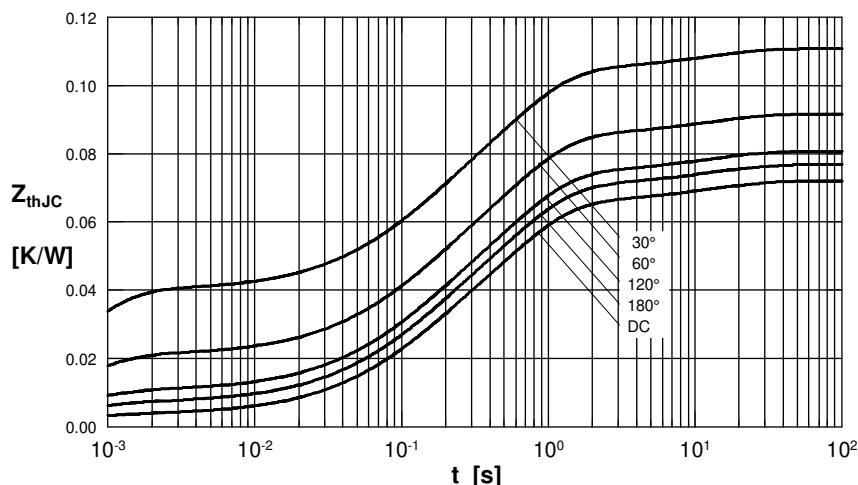


Fig. 9 Transient thermal impedance junction to case

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.072
180°	0.0768
120°	0.081
60°	0.092
30°	0.111

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.0067	12

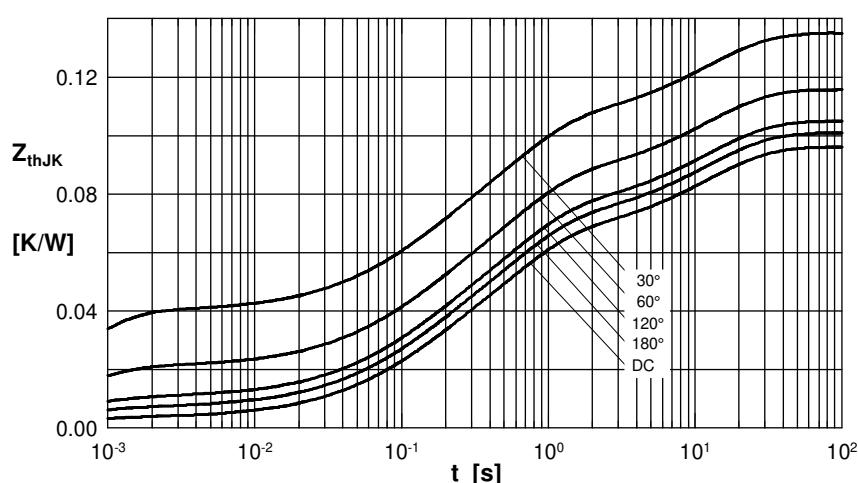


Fig.10 Transient thermal impedance junction to heatsink

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.096
180°	0.1
120°	0.105
60°	0.116
30°	0.135

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.0067	12
5	0.024	12



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Электрон
Связь**

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